In the Specification

Please amend the paragraph beginning on page 2, line 4, i.e. the paragraph corresponding to paragraph 0007 in the published application as follows:

On the other hand, according to the polycrystalline silicon technology, since the maximum temperature during the manufacturing steps thereof is high, i.e., about 1000°C., the mobility of carriers is about 30 to 100 $cm^2/V \cdot sec$. For example, a high temperature annealing process is required to convert amorphous silicon into polycrystalline silicon. Also, if TFTs manufactured by the polycrystalline silicon technology are used as the switching elements of pixels of a display panel of an active matrix-type LCD apparatus, a driver for driving the display panel can also be formed on the same substrate of the display panel, so that the above-mentioned ~~theremocompressing bonding process~~TAB or wire bonding process is unnecessary.

Please amend the paragraph beginning on page 2, line 19, i.e. the paragraph corresponding to paragraph 0008 in the published application as follows:

In the polycrystalline silicon technology, since the maximum temperature is high as stated above, the insulating substrate has to be a fused ~~quart~~ quartz substrate having a high melting temperature, for example. This would increase the manufacturing cost.

Please amend the paragraph beginning on page 4, line 28, i.e. the paragraph corresponding to paragraph 0020 in the published application as follows:

FIGS. 4A, 5A, 6A, 7A and ~~8B~~ 8A are cross-sectional views for explaining an embodiment of the method for manufacturing a TFT according to the present invention;

Please amend the paragraph beginning on page 8, line 24 and continuing onward to page 9, i.e., the paragraph corresponding to paragraph 0046 in the published application as follows:

Next, referring to FIGS. 5A and 5B, the glass substrate 1 is again subject to a cleaning and rinsing process to remove contaminants such as organic matter, metal, small particles and silicon oxide from the surface of the amorphous silicon layer 3. Then, the glass substrate 1 is entered into the pulse laser apparatus of FIG. 2 where the amorphous silicon layer 3 is irradiated with laser line beams under an atmosphere of pure nitrogen gas at a 700 Torr (8.33×10^4 Pa). In this case, the laser line beams have a rectangular size of 5 μm × 100 μm. Also, the energy of the laser beams is relatively high, for example, about 400 to 900 ~~mJ/am^2~~mJ/cm^2, and also, the slope of the energy with respect to the Y-direction is relatively sharp. As a result, as illustrated in FIG. 5B, crystalline silicon seeds (not shown) are randomly generated at portions of the amorphous silicon layer 3 at Y=Y1, Y2, Y1' and Y2' where the temperature is close to a melting point of silicon. Then, polycrystalline silicon is grown from the crystalline silicon seeds toward the center of each of the laser line beams at Y=Y3 and Y3'. Finally, the growth of polycrystalline silicon stops at Y=Y3 and Y3'. Thus, a polycrystalline silicon layer 3' is obtained to include elongated grains having a length of an approximately half of the width of the laser line beams. As a result, the polycrystalline silicon layer 3' has stripes each of which is divided into two regions 31 and 32. Then, nitrogen is exhausted from the pulse laser apparatus, and then, oxygen gas is introduced thereinto.